

N-Channel MOSFET

General Description

The WSP6024 is the highest performance trench N-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSP6024meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

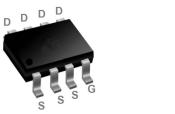
Product Summery

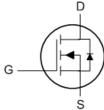
BVDSS	RDSON	ID
60V	8m Ω	15A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOP-8 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I₀@T₀=25℃	Continuous Drain Current, V _{GS} @ 10V ¹	15	A
I _D @T _C =70℃	Continuous Drain Current, V _{GS} @ 10V ¹	9.6	A
I _{DM} ^a	Pulsed Drain Current ²	43	Α
EAS ^b	Single Pulse Avalanche Energy ³	81	mJ
I _{AS} ^b	Avalanche Current	16	A
P _D @T _A =25℃	Total Power Dissipation ⁴	1.78	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	150	°C

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{θJA} ^c	Thermal Resistance Junction-ambient ¹		72	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹		1.2	°C/W

Note a : Pulse width limited by max. junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature $150^{\circ}C$ (initial temperature $T_i=25^{\circ}C$).

Note c : Surface Mounted on $1in^2$ pad area.



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Electrical Characteristics (T_J=25 $^{\circ}$ C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60			V	
$\triangle BV_{DSS} / \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$, I_D=1mA		0.044		V/℃	
Б	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =13A		8	10		
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V , I _D =8A		11	13.7	mΩ	
V _{GS(th)}	Gate Threshold Voltage		1.0	2.0	3.0	V	
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	—V _{GS} =V _{DS} , I _D =250uA		-4.6		mV/℃	
	Drain Source Lookage Current	V_{DS} =60V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1		
I _{DSS}	Drain-Source Leakage Current	V_{DS} =60V , V_{GS} =0V , T_{J} =55 $^{\circ}$ C			100	uA	
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm20V$, $V_{DS}=0V$			±100	nA	
Qg	Total Gate Charge (10V)			25.4			
Q _{gs}	Gate-Source Charge	V_{DS} =30V , V_{GS} =10V , I_{D} =6A		4.6		nC	
Q _{gd}	Gate-Drain Charge			3.8			
T _{d(on)}	Turn-On Delay Time			15			
Tr	Rise Time	V _{DD} =30V , V _{GEN} =10V ,		7			
T _{d(off)}	Turn-Off Delay Time	R _G =6Ω I _D =1A ,RL=30Ω		34		ns	
T _f	Fall Time			30			
Ciss	Input Capacitance			1500			
C _{oss}	Output Capacitance	V _{DS} =30V , V _{GS} =0V , f=1MHz		280		pF	
C _{rss}	Reverse Transfer Capacitance			40			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25℃			1.3	V
t _{rr}	Reverse Recovery Time			30		nS
Q _{rr}	Reverse Recovery Charge	l⊧=6.0A , dl/dt=100A/μs , Tյ=25℃		29		nC

Note d : Pulse test ; pulse width≤300ms, duty cycle≤2%.

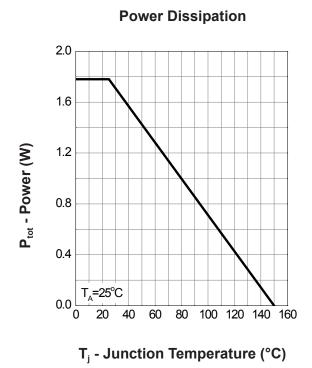
Note e : Guaranteed by design, not subject to production testing.

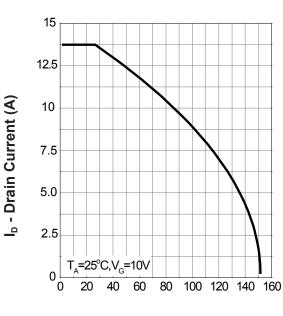


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Typical Characteristics





Drain Current

T_i - Junction Temperature (°C)

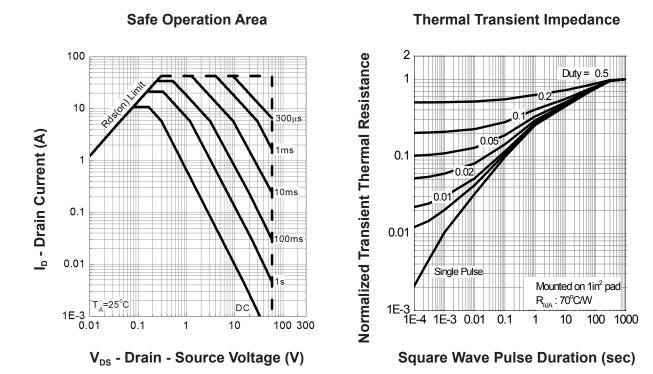
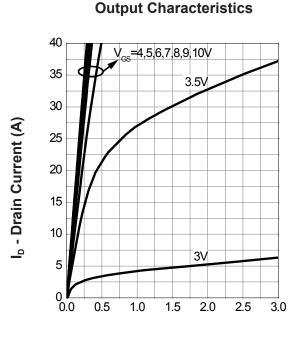


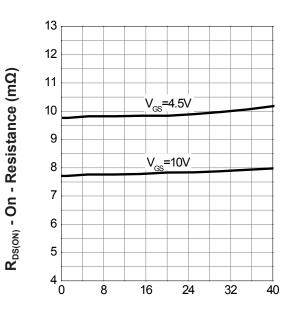
Fig5. Typical Source-Drain Diode Forward Voltage



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V_{DS} - Drain - Source Voltage (V)

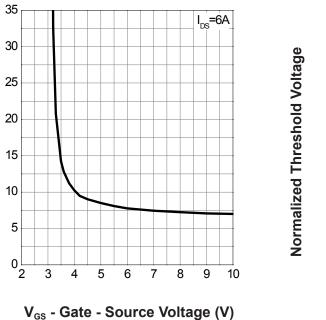


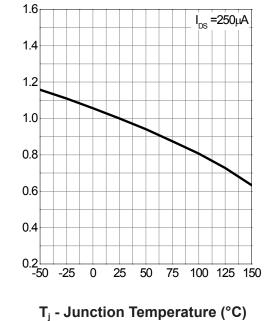
Drain-Source On Resistance

I_D - Drain Current (A)

Gate-Source On Resistance

Gate Threshold Voltage

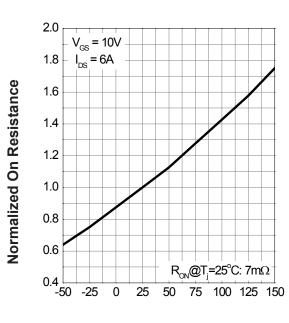




 $R_{\text{DS(ON)}}$ - On - Resistance (m $\Omega)$

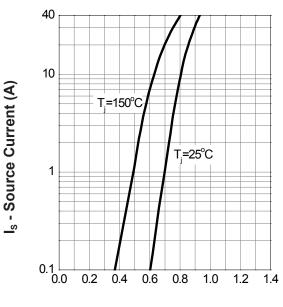


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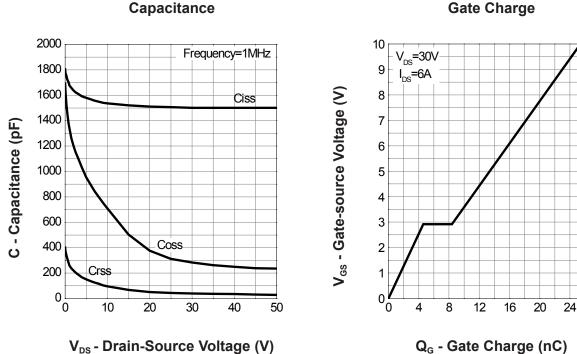
Drain-Source On Resistance

T_i - Junction Temperature (°C)



Source-Drain Diode Forward

V_{sp} - Source - Drain Voltage (V)



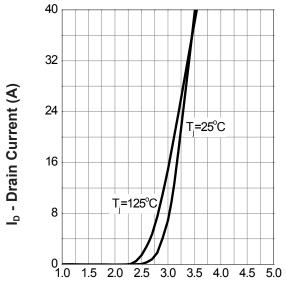
Gate Charge

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Transfer Characteristics

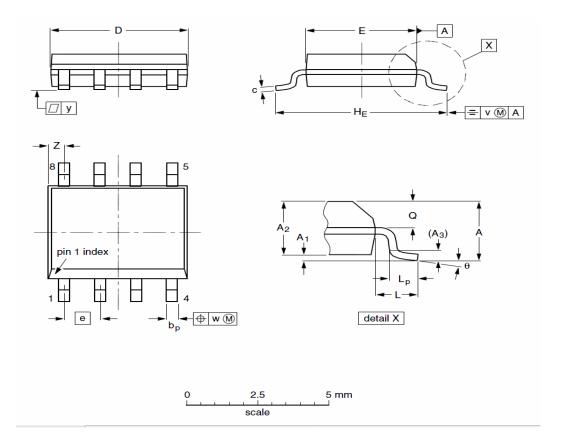
V_{GS} - Gate-Source Voltage (V)

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SOP8 Package Outline Data



Symbol	Min	Тур	Max	Symbol	Min	Тур	Max
A		1.75		A ₁	0.10	0.18	0.25
A ₂	1.25	1.35	1.45	A ₃		0.25	
b _p	0.36	0.42	0.49	С	0.19	0.22	0.25
D	4.80	4.92	5.00	E	3.80	3.90	4.00
е		1.27		HE	5.80	5.98	6.20
L		1.05		Lp	0.40	0.68	1.00
Q	0.60	0.65	0.70	v		0.25	
w		0.25		У		0.10	
Z	0.30	0.50	0.70	θ	0°		8°



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